

Features

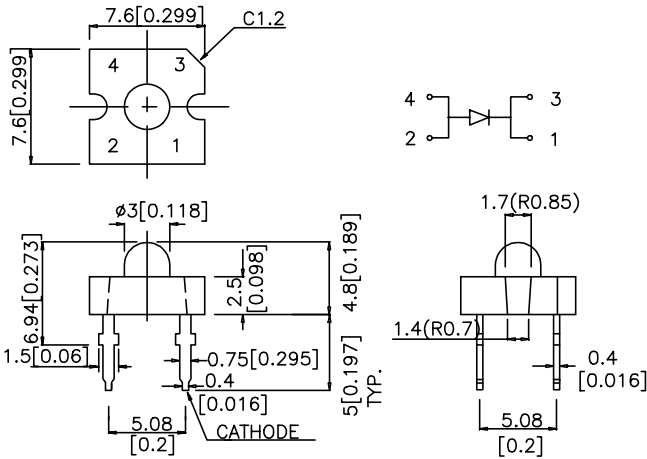
- SUPER FLUX OUTPUT.
- DESIGN FOR HIGH CURRENT OPERATION.
- OUTSTANDING MATERIAL EFFICIENCY.
- RELIABLE AND RUGGED.

L76761CSYC

Package Dimensions

Description

The Super Bright Yellow source color devices are made with DH InGaAlP on GaAs substrate Light Emitting Diode.



- Notes:
1. All dimensions are in millimeters (inches).
 2. Tolerance is $\pm 0.25(0.01)$ unless otherwise noted.
 3. Lead spacing is measured where the lead emerge package.
 4. Specifications are subjected to change without notice.

Selection Guide

Part No.	Dice	Lens Type	Iv (mcd) @ 20 mA *70mA		Viewing Angle
			Min.	Typ.	
L76761CSYC	SUPER BRIGHT YELLOW (InGaAlP)	WATER CLEAR	500	1000	20°
			*1900	*2700	20°

- NOTES FOR L76761C SERIES:
- *1. DRIVE CURRENT BETWEEN 10mA AND 30mA ARE RECOMMENDED FOR LONG TERM PERFORMANCE.
 - *2. OPERATION AT CURRENT BELOW 10mA IS NOT RECOMMENDED.

Electrical / Optical Characteristics at T_A=25°C

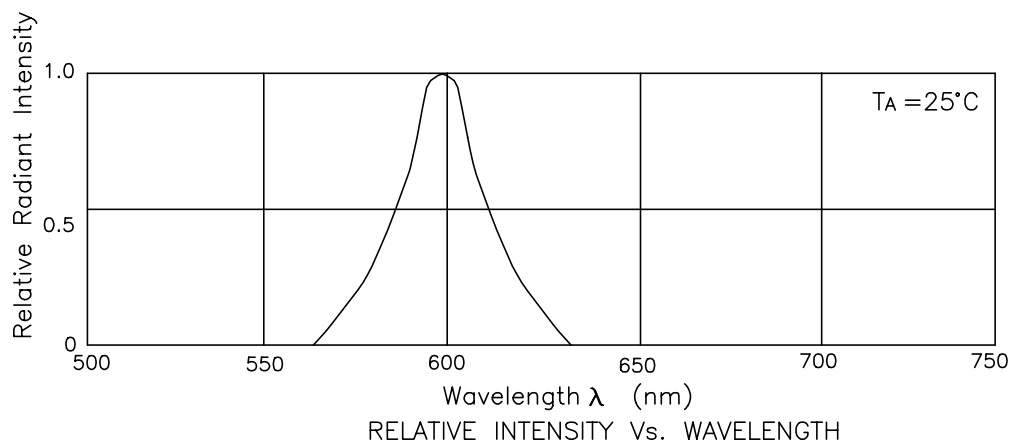
Symbol	Parameter	Device	Typ.	Max.	Units	Test Conditions
λ_{peak}	Peak Wavelength	Super Bright Yellow	590		nm	IF=20mA
$\Delta\lambda_{1/2}$	Spectral Line Halfwidth	Super Bright Yellow	20		nm	IF=20mA
C	Capacitance	Super Bright Yellow	33		pF	VF=0V;f=1MHz
V _F	Forward Voltage	Super Bright Yellow	2.0	2.4	V	IF=20mA
I _R	Reverse Current	All		10	uA	VR = 5V

Absolute Maximum Ratings at T_A=25°C

Parameter	Super Bright Yellow	Units
Power dissipation	125	mW
DC Forward Current	30	mA
Peak Forward Current [1]	150	mA
Reverse Voltage	5	V
Operating/Storage Temperature	-40°C To +85°C	
Lead Soldering Temperature [2]	260°C For 5 Seconds	

Notes:

1. 1/10 Duty Cycle, 0.1ms Pulse Width.
2. 4mm below package base.



L76761CSYC

